

## ABSTRACT OF THE DISCLOSURE

A method is specified for producing electric conductive structures for use in high frequency technology on a conductive structure carrier with layer spacings significantly less than 180  $\mu\text{m}$ (e.g., 30  $\mu\text{m}$ ) using microstrip conductors. In accordance with such method, a combination of a laser structuring method with an etching method in conjunction with a resist is used, which, at least with regard to the lasering with the laser structuring method, the etching with the etching method and the minimum thickness with which it can be applied to the conductive structure carrier, has properties which at least correspond to those of chemical tin or an amorphous resist.